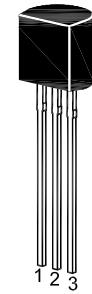
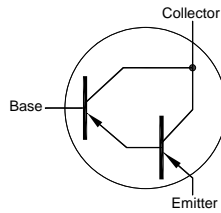


BC516

PNP Silicon Darlington Transistor



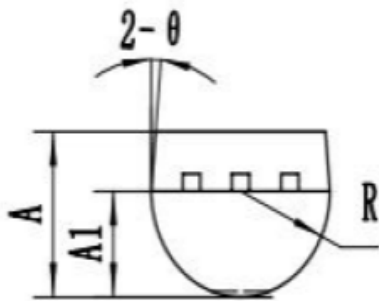
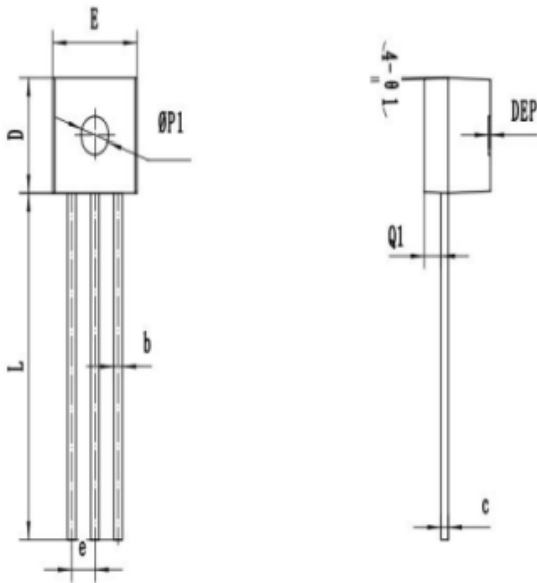
1. Collector 2. Base 3. Emitter
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	30	V
Emitter Base Voltage	$-V_{EBO}$	10	V
Collector Current (DC)	$-I_C$	500	mA
Peak Collector Current	$-I_{CM}$	800	mA
Total Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 2\text{ V}$, $-I_C = 20\text{ mA}$	h_{FE}	30000	-	-
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	100	nA
Emitter Base Cutoff Current at $-V_{EB} = 10\text{ V}$	$-I_{EBO}$	-	100	nA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	40	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	30	-	V
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	10	-	V
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 0.1\text{ mA}$	$-V_{CE(sat)}$	-	1	V
Base Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 0.1\text{ mA}$	$-V_{BE(sat)}$	-	1.5	V
Base Emitter On Voltage at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	$-V_{BE(on)}$	-	1.4	V
Transition Frequency at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	f_T	125	-	MHz



SYMBOL	MM		
	MIN	NOM	MAX
*A	3.00	3.25	3.50
A1	2.20	2.30	2.40
*b	0.40	0.45	0.50
*c	0.25	0.30	0.35
*D	4.50	4.60	4.70
*E	4.50	4.60	4.70
*e	1.22	1.27	1.32
*L	14.00	14.30	14.60
R	2.20	2.30	2.40
Q1	0.85	0.90	0.95
θ	3°	5°	7°
Ø1	1°	3°	5°
ØP1	1.40	1.50	1.60
DEP	0.05	0.10	0.20
带*为检验尺寸			